

PBRN123Y series

NPN 800 mA, 40 V BISS RETs; R1 = 2.2 k Ω , R2 = 10 k Ω

Rev. 01 — 27 February 2007

Product data sheet

1. Product profile

1.1 General description

800 mA NPN low V_{CEsat} Breakthrough In Small Signal (BISS) Resistor-Equipped Transistors (RET) family in small plastic packages.

Table 1. Product overview

Type number	Package		
	NXP	JEITA	JEDEC
PBRN123YK	SOT346	SC-59A	TO-236
PBRN123YS ^[1]	SOT54	SC-43A	TO-92
PBRN123YT	SOT23	-	TO-236AB

[1] Also available in SOT54A and SOT54 variant packages (see [Section 2](#)).

1.2 Features

- 800 mA output current capability
- High current gain h_{FE}
- Built-in bias resistors
- Simplifies circuit design
- Low collector-emitter saturation voltage V_{CEsat}
- Reduces component count
- Reduces pick and place costs
- $\pm 10\%$ resistor ratio tolerance

1.3 Applications

- Digital application in automotive and industrial segments
- Medium current peripheral driver
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_O	output current			^[1]		
	PBRN123YK, PBRN123YT		-	-	600	mA
	PBRN123YS		-	-	800	mA

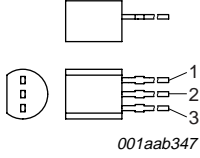
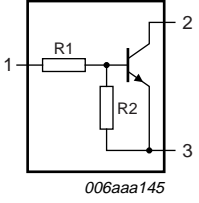
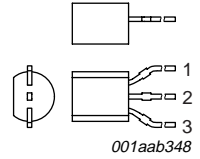
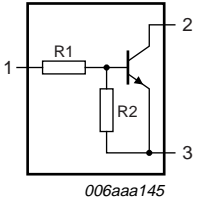
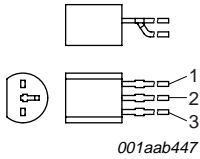
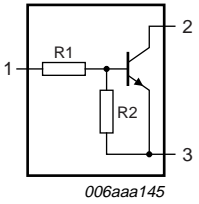
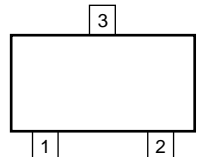
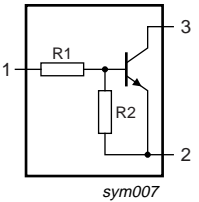
Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{ORM}	repetitive peak output current					
	PBRN123YK, PBRN123YT	$t_p \leq 1 \text{ ms}; \delta \leq 0.33$	-	-	800	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		4.1	4.55	5	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)	 <p>001aab347</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT54A			
1	input (base)	 <p>001aab348</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT54 variant			
1	input (base)	 <p>001aab447</p>	 <p>006aaa145</p>
2	output (collector)		
3	GND (emitter)		
SOT23; SOT346			
1	input (base)	 <p>006aaa144</p>	 <p>sym007</p>
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PBRN123YK	SC-59A	plastic surface-mounted package; 3 leads	SOT346
PBRN123YS ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PBRN123YT	-	plastic surface-mounted package; 3 leads	SOT23

[1] Also available in SOT54A and SOT54 variant packages (see [Section 2](#) and [Section 9](#)).

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PBRN123YK	G7
PBRN123YS	N123YS
PBRN123YT	*7P

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

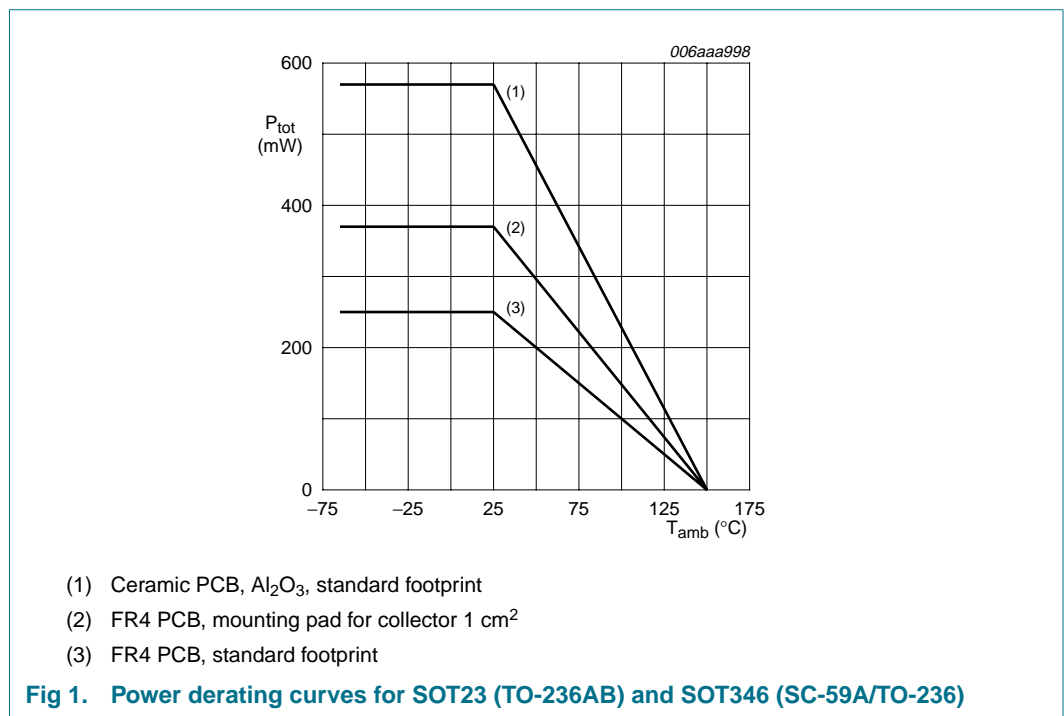
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	40	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
V_I	input voltage				
	positive		-	+22	V
	negative		-	-5	V
I_O	output current				
	PBRN123YK, PBRN123YT		^[1] -	600	mA
			^[2] ^[3] -	700	mA
	PBRN123YS		^[1] -	800	mA
I_{ORM}	repetitive peak output current				
	PBRN123YK, PBRN123YT	$t_p \leq 1$ ms; $\delta \leq 0.33$	-	800	mA

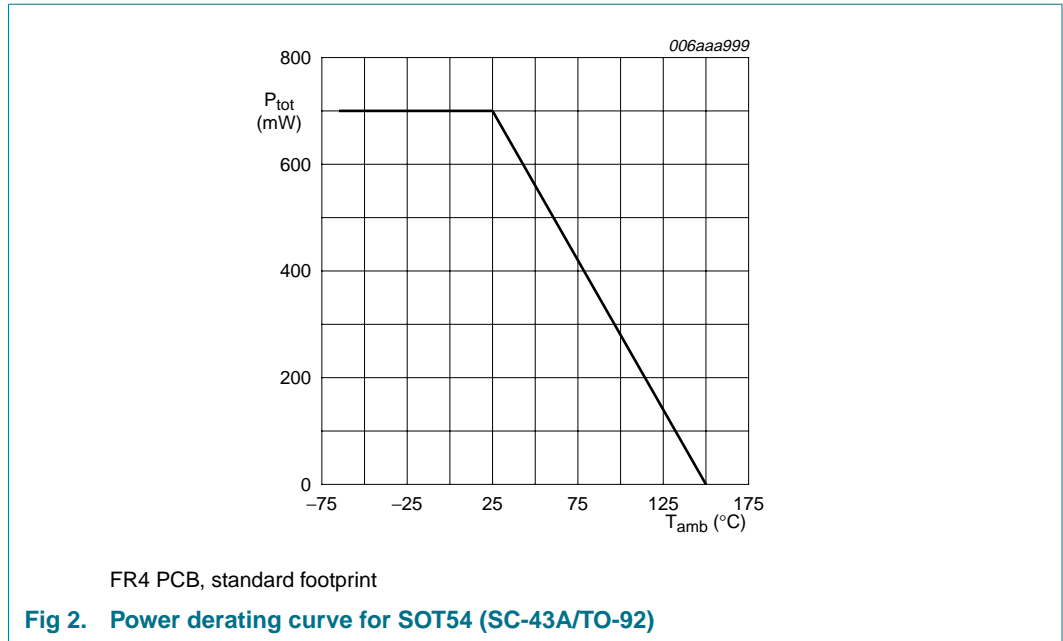
Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C					
			PBRN123YK, PBRN123YT	[1]	-	250	mW
				[2]	-	370	mW
				[3]	-	570	mW
	PBRN123YS		[1]	-	700	mW	
T _j	junction temperature		-	150	°C		
T _{amb}	ambient temperature		-65	+150	°C		
T _{stg}	storage temperature		-65	+150	°C		

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





6. Thermal characteristics

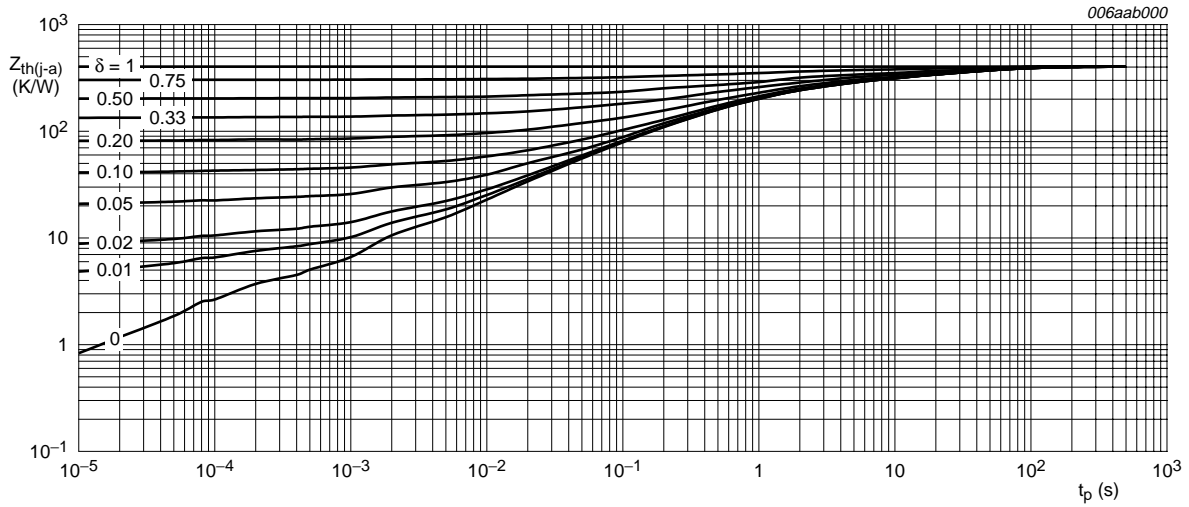
Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
R _{th(j-a)}	thermal resistance from junction to ambient	in free air						
			PBRN123YK, PBRN123YT	[1]	-	-	500	K/W
				[2]	-	-	338	K/W
				[3]	-	-	219	K/W
	PBRN123YS		[1]	-	-	179	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point							
		PBRN123YK, PBRN123YT		-	-	105	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

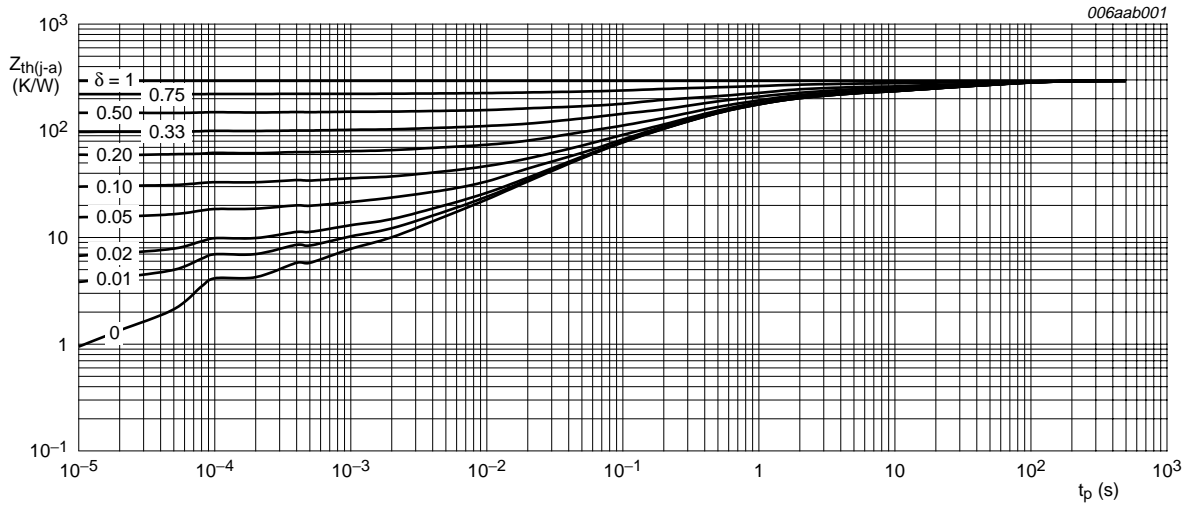
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



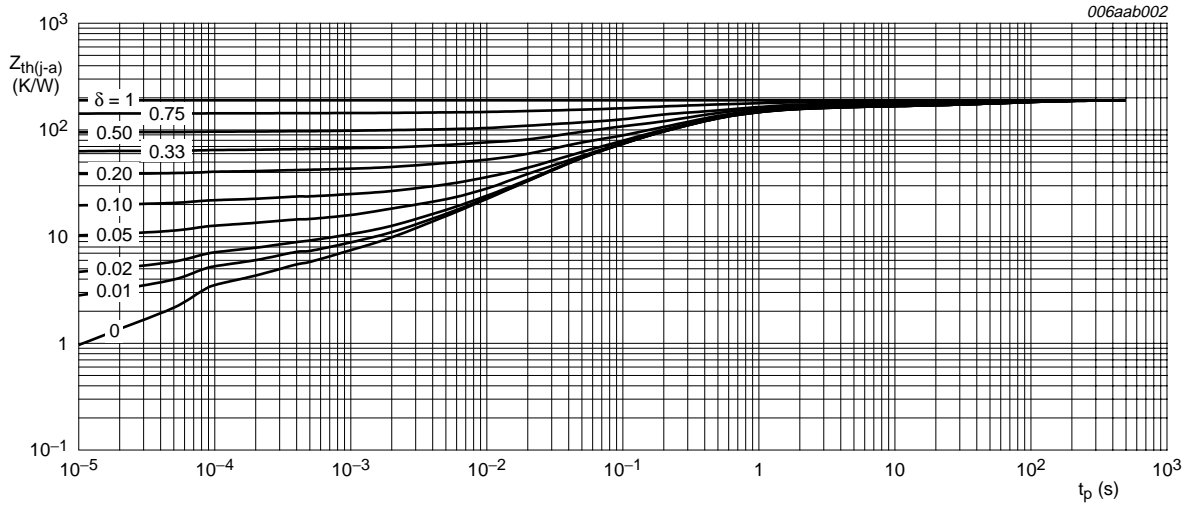
FR4 PCB, standard footprint

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB) and SOT346 (SC-59A/TO-236); typical values



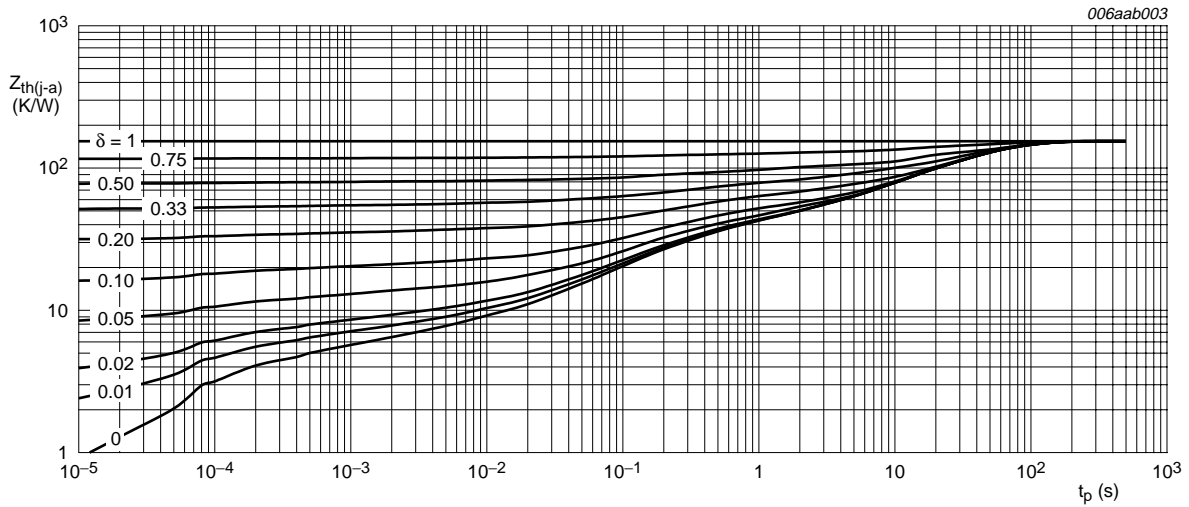
FR4 PCB, mounting pad for collector 1 cm²

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB) and SOT346 (SC-59A/TO-236); typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB) and SOT346 (SC-59A/TO-236); typical values



FR4 PCB, standard footprint

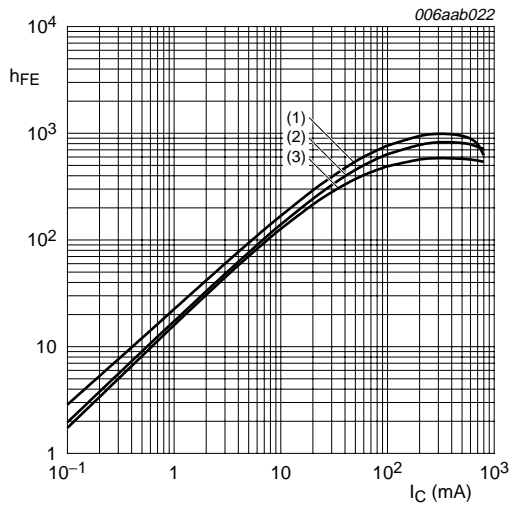
Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT54 (SC-43A/TO-92); typical values

7. Characteristics

Table 8. Characteristics
T_{amb} = 25 °C unless otherwise specified.

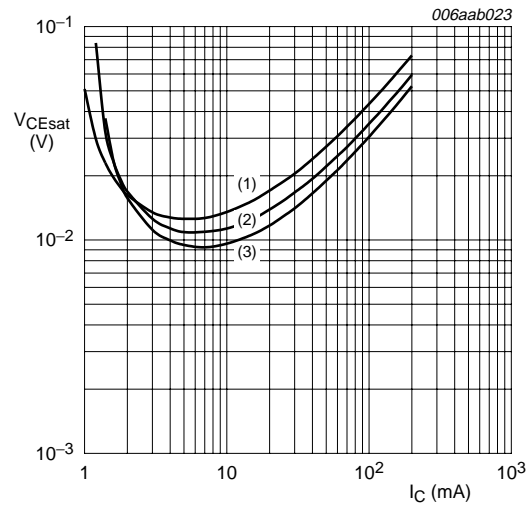
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0 A	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	-	-	0.5	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	0.65	mA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 50 mA	300	450	-	
		V _{CE} = 5 V; I _C = 300 mA	[1] 500	750	-	
		V _{CE} = 5 V; I _C = 600 mA	[1] 500	720	-	
		V _{CE} = 5 V; I _C = 800 mA	[1] 450	650	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 50 mA; I _B = 2.5 mA	-	25	35	mV
		I _C = 200 mA; I _B = 10 mA	-	60	85	mV
		I _C = 500 mA; I _B = 10 mA	[1] -	160	220	mV
		I _C = 600 mA; I _B = 6 mA	[1] -	270	550	mV
		I _C = 800 mA; I _B = 8 mA	[1] -	0.56	1.15	V
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μ A	0.4	0.6	1	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA	0.5	0.8	1.4	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	k Ω
R2/R1	bias resistor ratio		4.1	4.55	5	
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0 A; f = 1 MHz	-	7	-	pF

[1] Pulse test: t_p \leq 300 μ s; δ \leq 0.02.



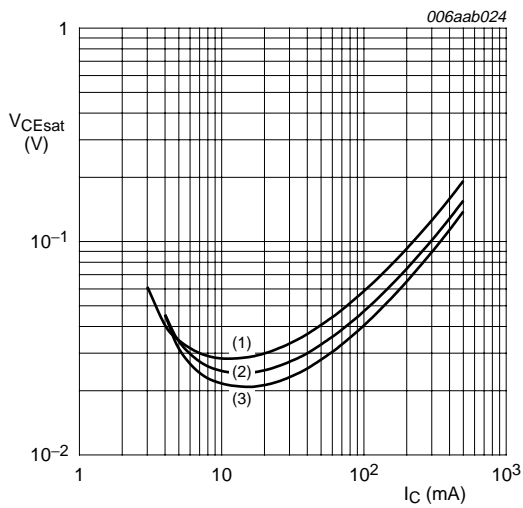
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 7. DC current gain as a function of collector current; typical values



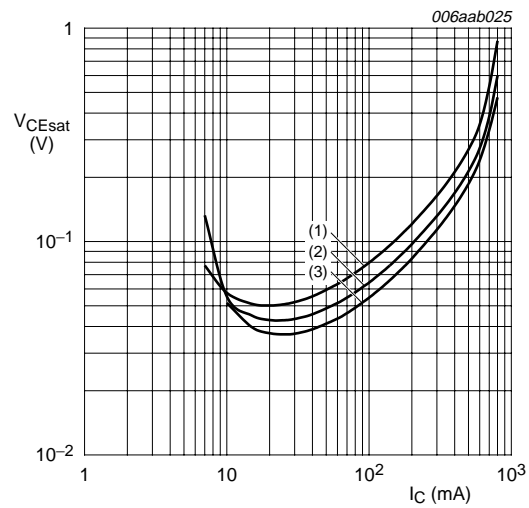
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



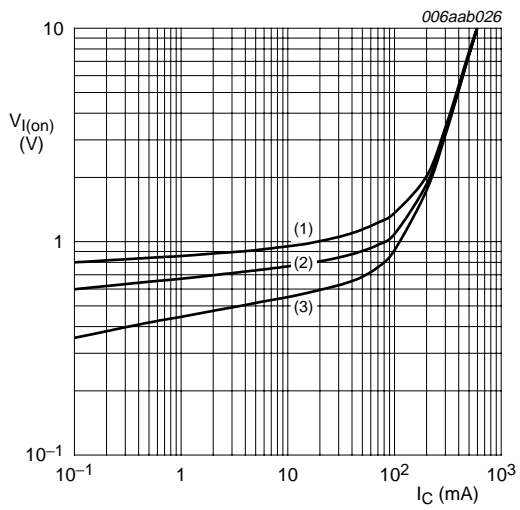
$I_C/I_B = 50$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



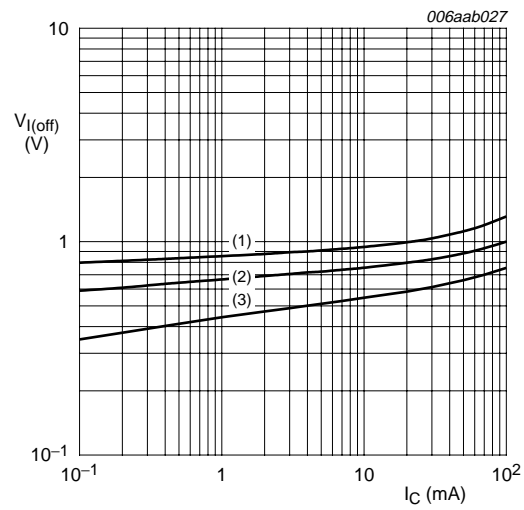
$I_C/I_B = 100$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -40\text{ }^{\circ}\text{C}$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

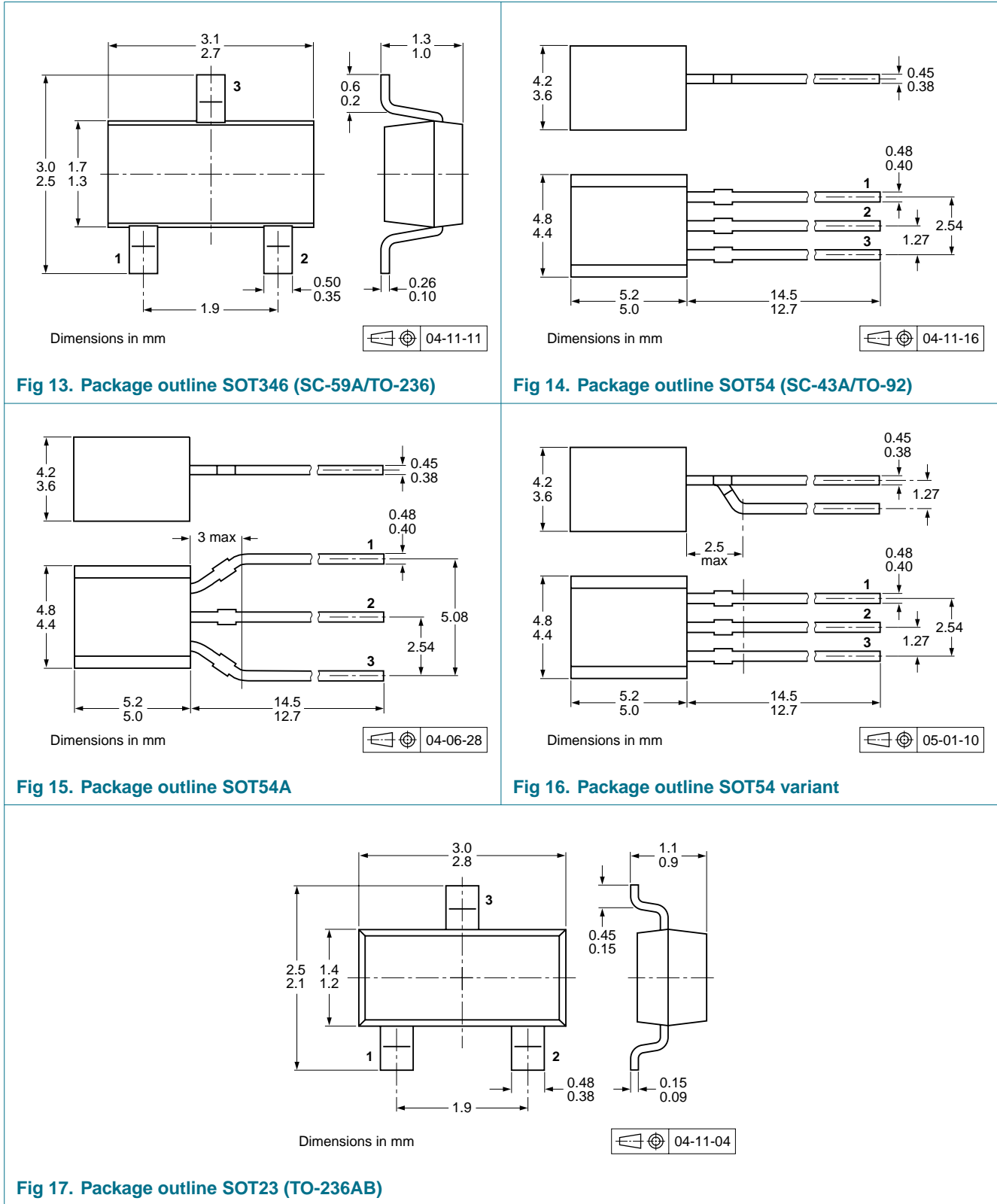
Fig 11. On-state input voltage as a function of collector current; typical values



$V_{CE} = 5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig 12. Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

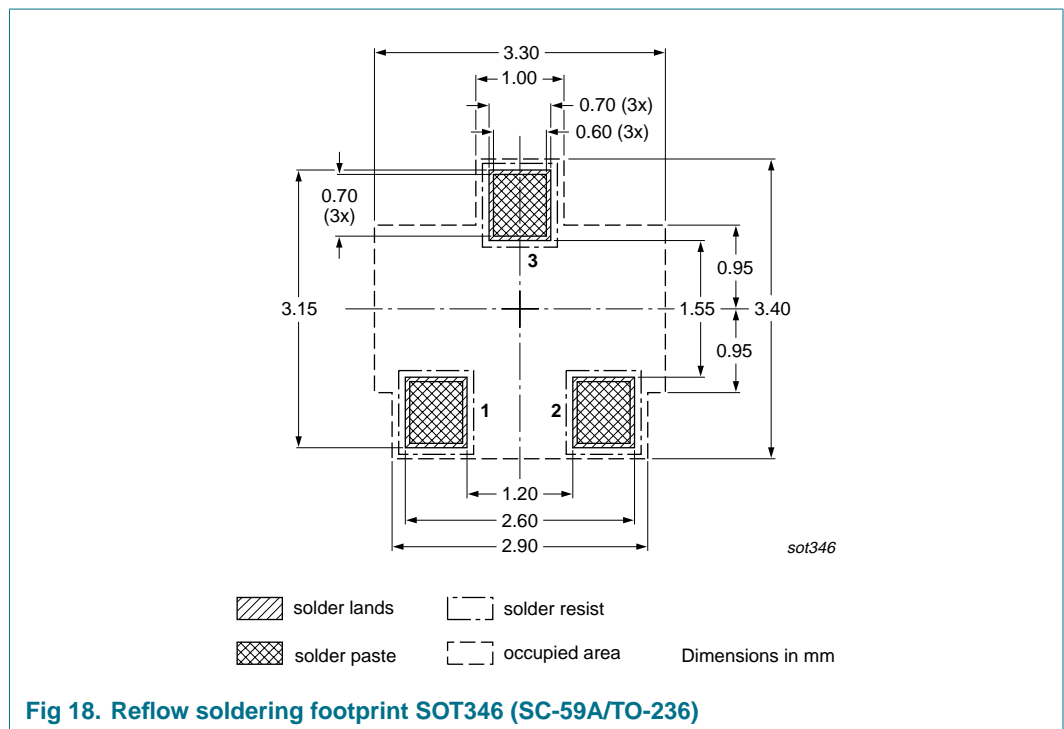
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PBRN123YK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PBRN123YS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PBRN123YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

[1] For further information and the availability of packing methods, see [Section 13](#).

10. Soldering



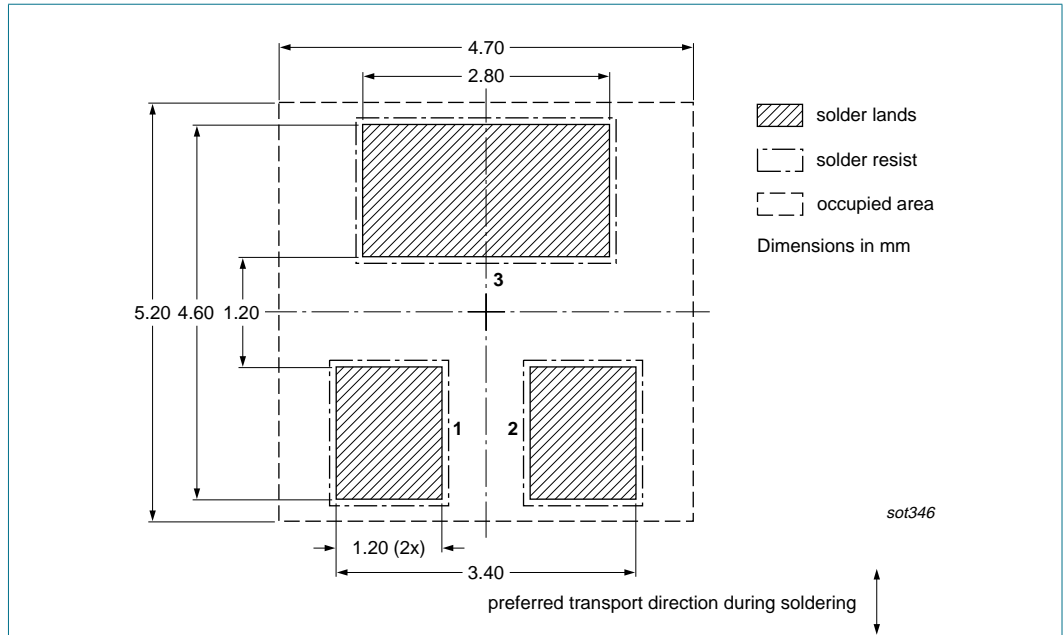


Fig 19. Wave soldering footprint SOT346 (SC-59A/TO-236)

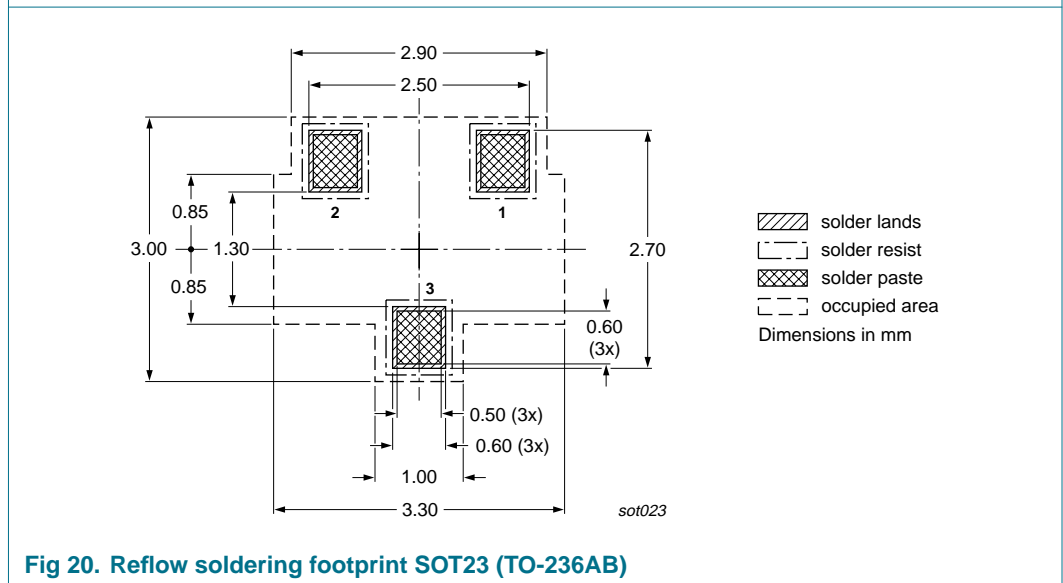
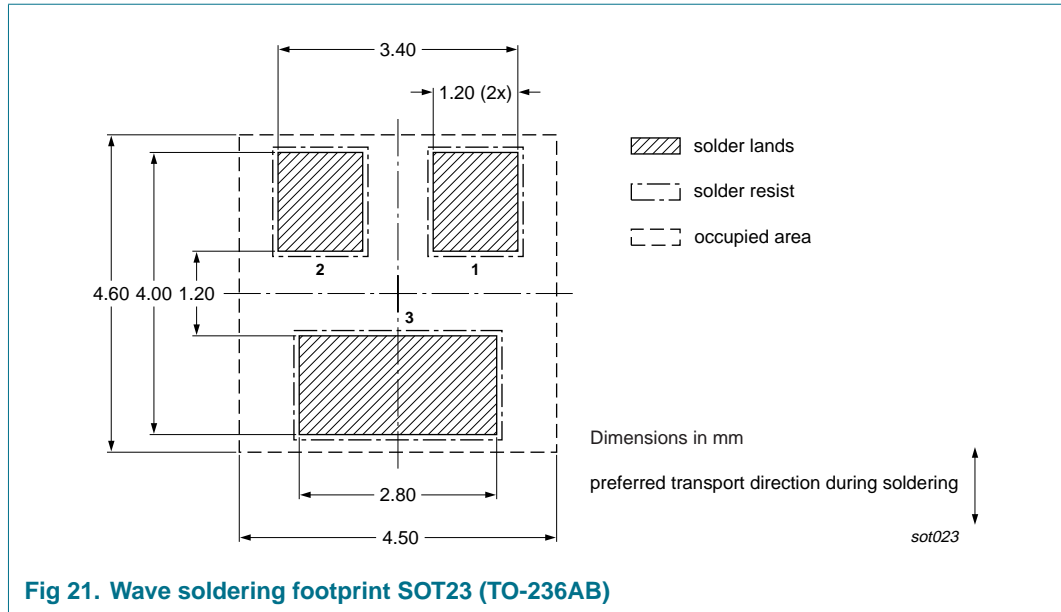


Fig 20. Reflow soldering footprint SOT23 (TO-236AB)



11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBRN123Y_SER_1	20070227	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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